Ordering number:EN4665

PNP Epitaxial Planar Silicon Transistor

2SA1838

Muting Circuit Applications

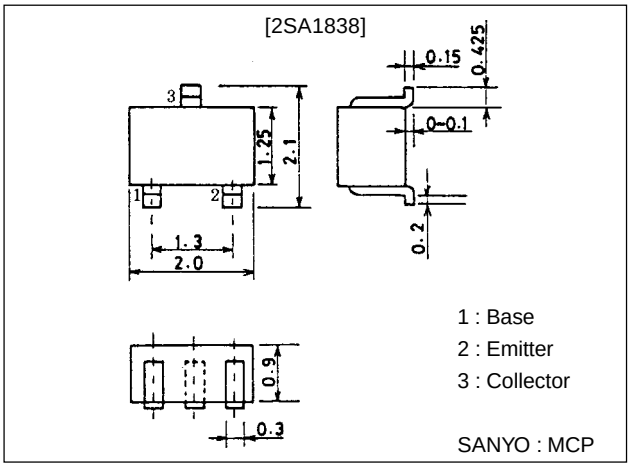
Features

- Very small-sized package permitting 2SA1838-applied sets to be made small and slim.
- Small output capacitance.
- Low collector-to-emitter saturation voltage.
- Low ON resistance.

Package Dimensions

unit:mm

2059A



Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		–15	V
Collector-to-Emitter Voltage	V_{CEO}		–10	V
Emitter-to-Base Voltage	V_{EBO}		–5	V
Collector Current	I_C		–100	mA
Colletor Current (Pulse)	I_{CP}		–200	mA
Base Current	I_B		–20	mA
Collector Dissipation	P_C		200	mW
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=–12V, I_E=0			–0.1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=–4V, I_C=0			–0.1	μA
DC Current Gain	h_{FE}	V_{CE}=–2V, I_C=–5mA	200		600	
Gain-Bandwidth Product	f_T	V_{CE}=–5V, I_C=–10mA		600		MHz
Output Capacitance	C_{ob}	V_{CB}=–10V, f=1MHz		0.9		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=–10mA, I_B=–1mA		–0.04	–0.15	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=–10mA, I_B=–1mA		–0.82	–1.1	V

Marking : LS

SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=–10μA, I_E=0	–15			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=–1mA, R_{BE}=∞	–10			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=–10μA, I_C=0	–5			V
On Resistance	R_{on}	I_B=–3mA, f=1MHz		3.0		Ω